

QS5U28

- 1) The QS5U28 combines Pch Treueh MOSFET with a Schottky barrier diode in a single TSMT5 package.
- 2) Pch Treueh MOSFET have a low on-state resistance with a fast switching.
- 3) Pch Treueh MOSFET is neucted a low voltage drive (2.5V).
- 4) The independently connected Schottky barrier diode have a low forward voltage.

load switch, DC/DC conversion

- Silicon P-channel MOS FET
- Schottky Barrier DIODE

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QS5U28		○

[illegible]

The diagram shows a MOSFET with its Gate connected to terminal (1), Source to terminal (2), and Drain to terminal (4). An ESD protection diode, labeled *1, is connected between the Gate and Source. A body diode, labeled *2, is shown as a diode symbol with an arrow pointing from the Drain to the Source. A legend on the right identifies the terminals: (1) Gate, (2) Source, (3) Anode, (4) Cathode, and (5) Drain.

(1) Gate
(2) Source
(3) Anode
(4) Cathode
(5) Drain

*1 ESD protection diode
*2 Body diode

* A protection diode has been built in between the gate and the source to protect against static electricity when the product is in use. Use the protection circuit when rated voltages are exceeded.

Transistor

●Absolute maximum ratings (Ta=25°C)

<MOSFET>

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	−20	V
Gate-source voltage	V _{GSS}	±12	V
Drain current	Continuous	I _D	±2.0
	Pulsed	I _{DP}	±8.0
Source current (Body diode)	Continuous	I _S	−1.0
	Pulsed	I _{SP}	−8.0
Channel temperature	T _{ch}	150	°C
Power dissipation	P _D	0.9	W/ELEMENT*3

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Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	V _{RM}	25	V
Reverse voltage	V _R	20	V
Forward current	I _F	1.0	A
Forward current surge peak	I _{FSM}	3.0	A*2
Junction temperature	T _j	150	°C
Power dissipation	P _D	0.7	W/ELEMENT*3

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Parameter	Symbol	Limits	Unit
Total power dissipation	P _D	1.25	W/TOTAL*3
Range of storage temperature	T _{stg}	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1% *2 60Hz·1cyc. *3 Mounted on a ceramic board.

●Electrical characteristics (Ta=25°C)

<MOSFET>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	−	−	±10	μA	V _{GS} = ±12V, V _{DS} = 0V
Drain-source breakdown voltage	V _{(BR)DSS}	−20	−	−	V	I _D = −1mA, V _{GS} = 0V
Zero gate voltage drain current	I _{DSS}	−	−	−1	μA	V _{DS} = −20V, V _{GS} = 0V
Gate threshold voltage	V _{GS(th)}	−0.7	−	−2.0	V	V _{DS} = −10V, I _D = −1mA
Static drain-source on-state resistance	R _{DS(on)}	−	90	125	mΩ	I _D = −2A, V _{GS} = −4.5V
		−	97	135	mΩ	I _D = −2A, V _{GS} = −4.0V
		−	175	245	mΩ	I _D = −1A, V _{GS} = −2.5V
Forward transfer admittance	Y _{fs}	1.6	−	−	S	V _{DS} = −10V, I _D = −1A*
Input capacitance	C _{iss}	−	450	−	pF	V _{DS} = −10V
Output capacitance	C _{oss}	−	70	−	pF	V _{GS} = 0V
Reverse transfer capacitance	C _{rss}	−	52	−	pF	f=1MHz
Turn-on delay time	t _{d(on)}	−	10	−	ns	V _{DD} ≐ −15V V _{GS} = −4.5V
Rise time	t _r	−	16	−	ns	I _D = −1A
Turn-off delay time	t _{d(off)}	−	32	−	ns	R _L ≐ 15Ω
Fall time	t _f	−	15	−	ns	R _G = 10Ω
Total gate charge	Q _g	−	4.8	−	nC	V _{DD} ≐ −15V V _{GS} = −4.5V
Gate-source charge	Q _{gs}	−	1.0	−	nC	I _D = −2A
Gate-drain charge	Q _{gd}	−	1.3	−	nC	R _L ≐ 7.5Ω R _G = 10Ω

<MOSFET> Body diode (Source-drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	−	−	−1.2	V	I _S = −1.0V, V _{GS} = 0V

* Pulsed

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Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	−	−	0.45	V	I _S = −1.0V
Reverse leakage	I _R	−	−	200	μA	V _R = 20V

Transistor

●Electrical characteristic curves

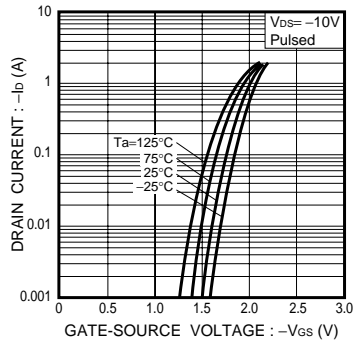


Fig.1 Typical Transfer Characteristics

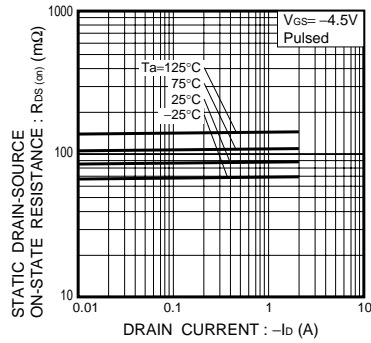


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (I)

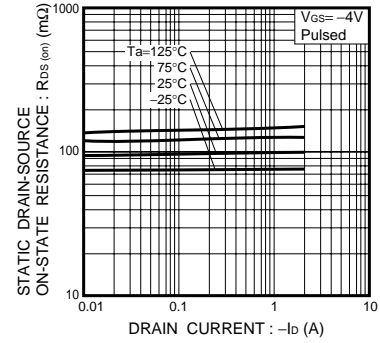


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (II)

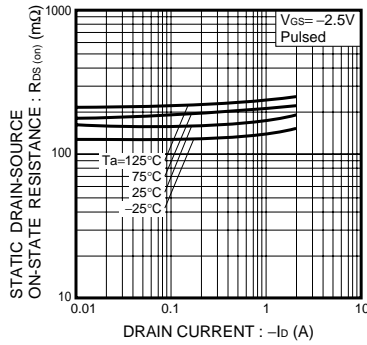


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (III)

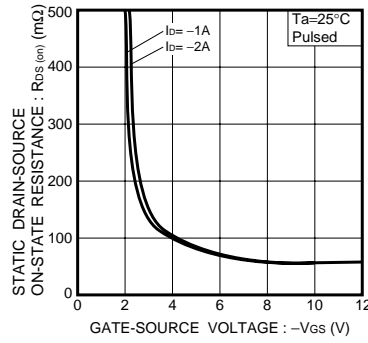


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

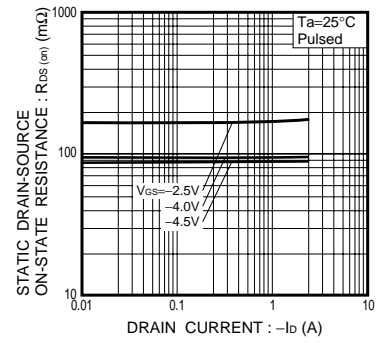


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

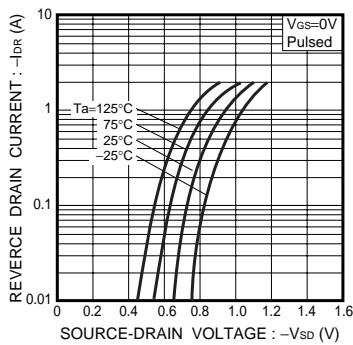


Fig.7 Reverse Drain Current vs. Source-Drain Voltage

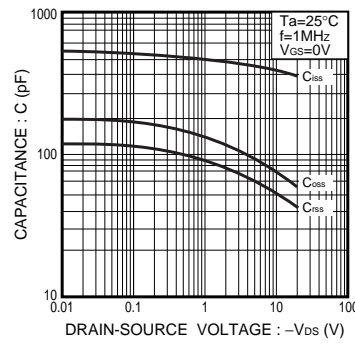


Fig.8 Typical Capacitance vs. Drain-Source Voltage

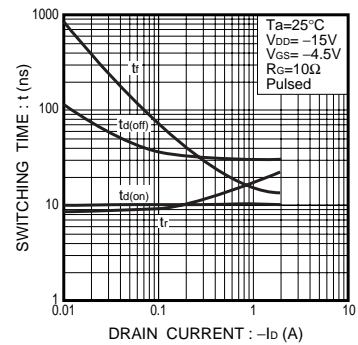


Fig.9 Switching Characteristics

Transistor

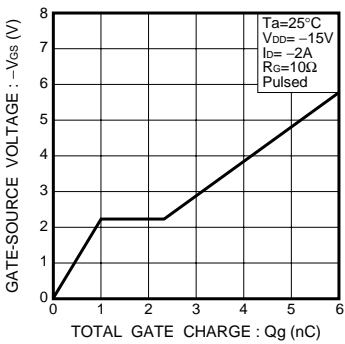


Fig.10 Dynamic Input Characteristics

●Measurement circuits

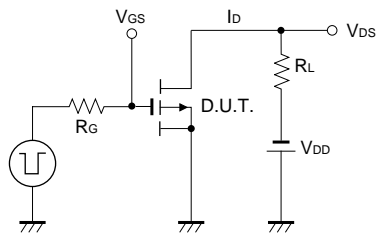


Fig.11 Switching Time Measurement Circuit

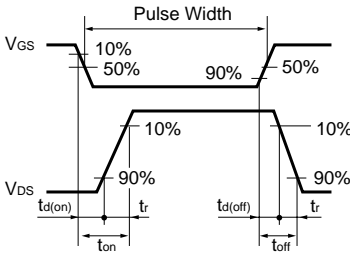


Fig.12 Switching Waveforms

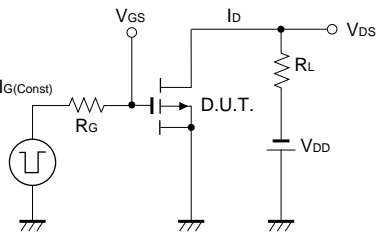


Fig.13 Gate Charge Measurement Circuit

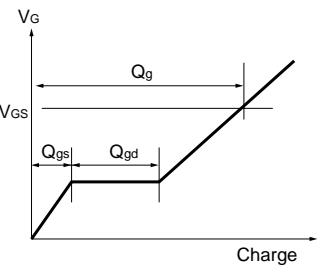


Fig.14 Gate Charge Waveforms

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